

TPR 700

700 Watts, 50 Volts, Pulsed
Avionics 1030 – 1090 MHz

GENERAL DESCRIPTION

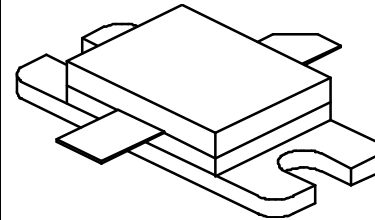
The TPR 700 is a high power COMMON BASE bipolar transistor. It is designed for pulsed systems in the frequency band 1030-1090 MHz. The device has gold thin-film metallization for proven highest MTTF. The transistor includes input returns for **fast rise time**. Low thermal resistance package reduces junction temperature, extends life.

ABSOLUTE MAXIMUM RATINGS

Maximum Power Dissipation @ 25°C ²		2050 Watts
Maximum Voltage and Current		
BVces	Collector to Base Voltage	65 Volts
BVebo	Emitter to Base Voltage	3.5 Volts
Ic	Collector Current	55 Amps
Maximum Temperatures		
Storage Temperature		- 65 to + 200°C
Operating Junction Temperature		+ 200°C

CASE OUTLINE

**55KT, Style 1
Common Base**



ELECTRICAL CHARACTERISTICS @ 25 °C

SYMBOL	CHARACTERISTICS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
P_{out}	Power Out	F = 1030 MHz	700			Watts
P_{in}	Power Input	V _{cc} = 50 Volts			150	Watts
P_g	Power Gain	PW = 10 µsec	6.7	35		dB
h_c	Collector Efficiency	DF = 1%			70	%
t_r	Rise Time				30:1	ns
VSWR	Load Mismatch Tolerance	F = 1030 MHz				
BVebo³	Emitter to Base Breakdown	I _e = 50mA	3.5			Volts
BVces	Collector to Emitter Breakdown	I _c = 100mA	65			Volts
h_{FE}	DC - Current Gain	I _c = 1000mA, V _{ce} = 5 V	10			
qjc²	Thermal Resistance				0.08	°C/W

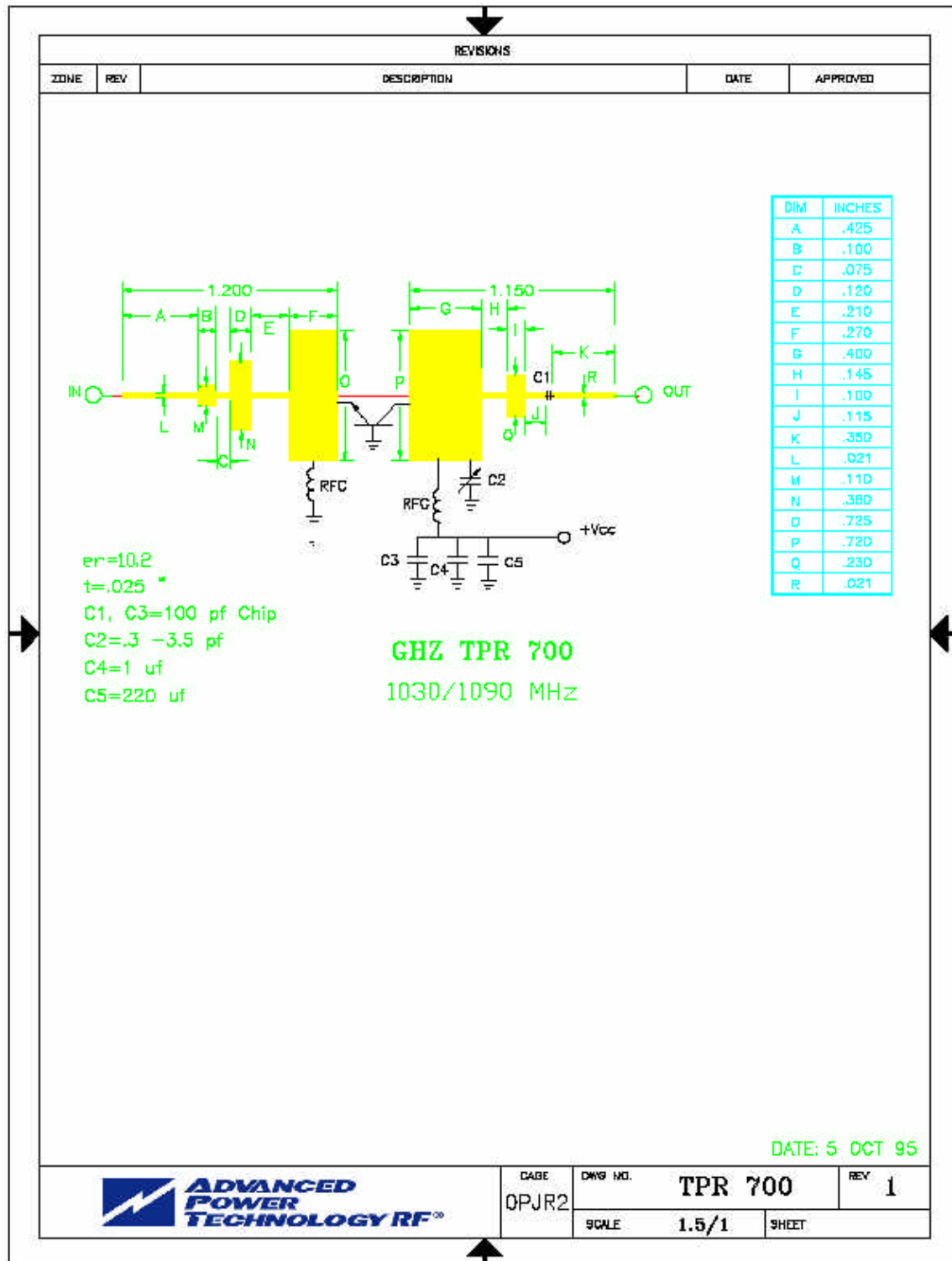
Note 1: At rated output power and pulse conditions

2: At rated pulse conditions

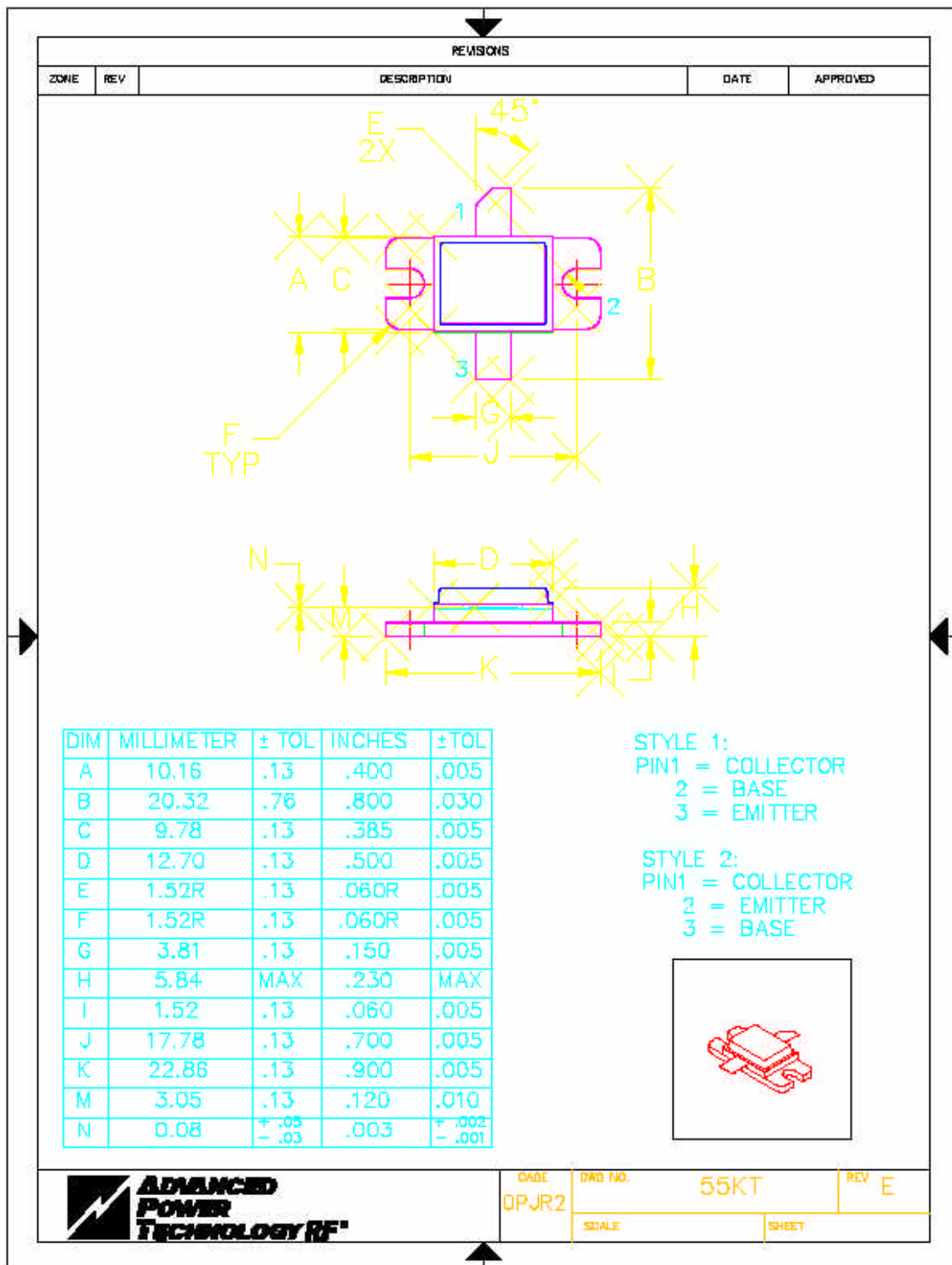
3: Cannot measure due to input return

Rev A. – Sept 2005

TPR700



TPR700



Advanced Power Technology reserves the right to change, without notice, the specifications and information contained herein. Visit our web site at www.advancedpower.com or contact our factory direct.